



30V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
	11mΩ @ V _{GS} = -10V	-13A
-30V	17mΩ @ V _{GS} = -4.5V	-9.9A

Description

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

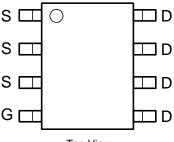
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram
- Terminals: Finish—Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.074g (Approximate)

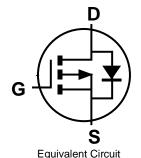




Top View



Top View Internal Schematic



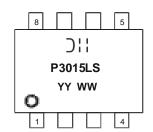
Ordering Information (Note 5)

Part Number	Case	Packaging
DMP3015LSSQ-13	SO-8	2500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q10x and standard products are electrically and thermally the same, except where specified. For more information, please refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



The Manufacturer's Marking
P3015LS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 18 = 2018)
WW = Week (01 - 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	V	
Gate-Source Voltage			V _{GSS}	±20	V
Drain Current (Note 6)	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	-13 -9.75	А
Pulsed Drain Current (Note 7)			I _{DM}	-45	Α

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_{D}	2.5	W
Thermal Resistance, Junction to Ambient	$R_{\Theta JA}$	50	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 6. Device mounted on 2 oz. Copper pads on FR-4 PCB with $R_{\Theta JA} = +50^{\circ}$ C/W.
- 7. Pulse width ≤10µS, Duty Cycle ≤1%.

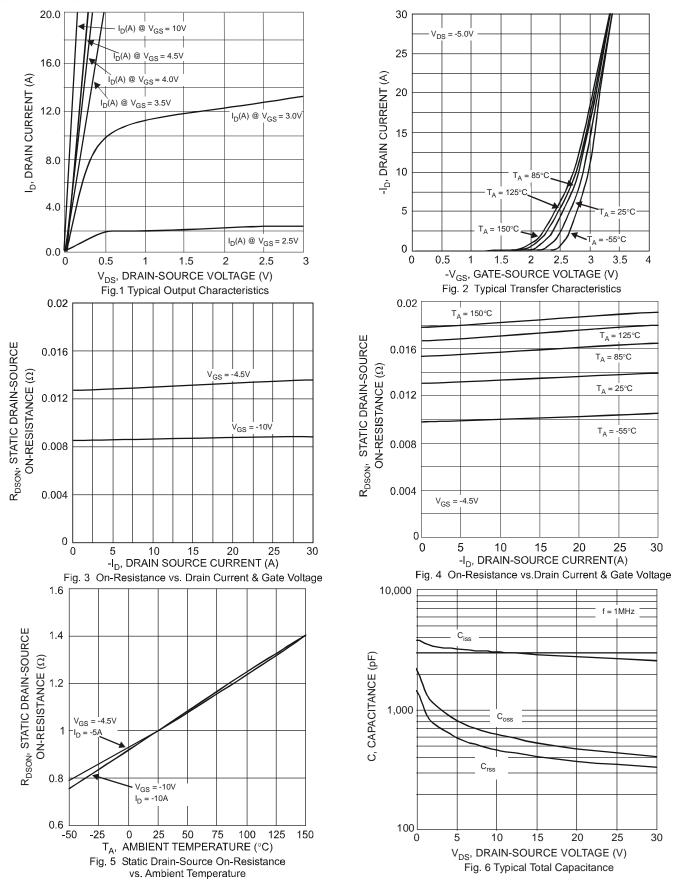
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	-	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(th)}$	-1	1	-2	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	D-s/s/iii	_	9	11	mΩ	$V_{GS} = -10V, I_D = -13A$
Static Diani-Source On-Resistance	R _{DS(ON)}	_	14	17	11152	$V_{GS} = -4.5V, I_D = -10A$
Forward Transconductance	9fs	_	15		S	$V_{DS} = -15V, I_{D} = -8A$
Diode Forward Voltage (Note 8)	V _{SD}	-0.5	1	-1.1	V	$V_{GS} = 0V, I_{S} = -2.1A$
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	_	2,748	l	pF	V 00V V 0V
Output Capacitance	Coss	_	357		pF	$V_{DS} = -20V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	_	356	l	pF	1 = 1.0101112
Gate Resistance	R_{G}	_	2.0		Ω	$V_{DS} = 0V$, $V_{GS} = 0V$ f = 1.0MHz
SWITCHING CHARACTERISTICS (Note 9)						
Total Gate Charge	Qg	_	30.0	1	nC	$V_{DS} = -10V$, $V_{GS} = -4.5V$, $I_{D} = -13A$
Total Gate Charge		_	60.4	-		$V_{DS} = -10V$, $V_{GS} = -10V$, $I_{D} = -13A$
Gate-Source Charge	Q_{gs}	_	7.2	l	110	$V_{DS} = -10V$, $V_{GS} = -10V$, $I_{D} = -13A$
Gate-Drain Charge	Q_{gd}	_	16.4			$V_{DS} = -10V$, $V_{GS} = -10V$, $I_{D} = -13A$
Turn-On Delay Time	t _{d(on)}	_	11.2	_		
Rise Time	t _r	_	12.4	_	nS	$V_{DS} = -15V, V_{GS} = -10V,$
Turn-Off Delay Time	t _{d(off)}	_	104.9		113	$I_D = -1A, R_G = 6.0\Omega$
Fall Time	t _f	_	61.7	1		

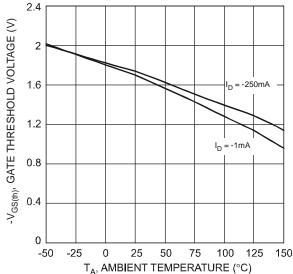
Notes:

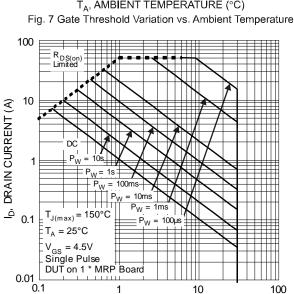
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.











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 $\rm V_{DS}$, DRAIN-SOURCE VOLTAGE (V) Figure 9 SOA, Safe Operation Area

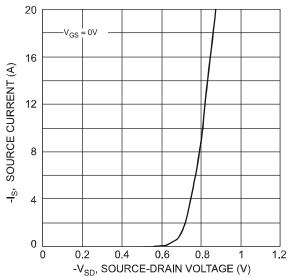
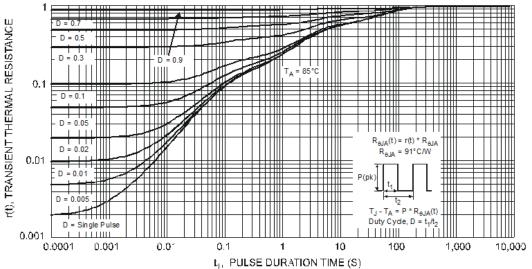


Fig. 8 Forward Drain Current vs. Source-Drain Voltage



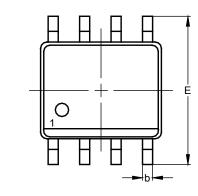
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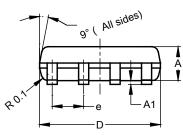
Fig. 10 Transient Thermal Resistance

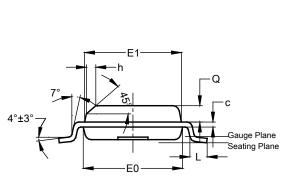


Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.







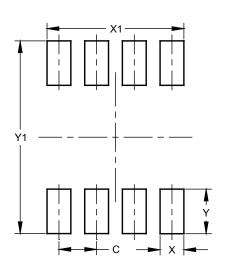
SO-8

SO-8

SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
b	0.30	0.50	0.40		
С	0.15	0.25	0.20		
D	4.85	4.95	4.90		
E	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е	e — — 1.27				
h	1	_	0.35		
L	0.62	0.82	0.72		
Q	0.60	0.70	0.65		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	1.27		
Х	0.802		
X1	4.612		
Υ	1.505		
Y1	6.50		



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